Power Transistor (-160V, -1.5A) 2SB1275 / 2SB1236A

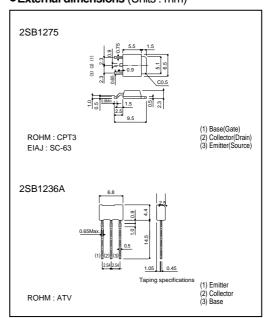
Features

- 1) High breakdown voltage.(BVcEo = -160V)
- 2) Low collector output capacitance. (Typ. 30pF at $V_{CB} = 10V$)
- 3) High transition frequency.($f_T = 50MHz$)
- 4) Complements the 2SD1918 / 2SD1857A.

● Absolute maximum ratings (Ta = 25°C)

	Parameter	Symbol	Limits	Unit		
Collector-base voltage		Vсво	-160	V		
Collector-e	mitter voltage	Vceo	-160	V		
Emitter-base voltage		VEBO	-5	V		
Collector current		Ic	-1.5	A(DC)		
		IC IC	-3	A(Pulse) *1		
Collector	2SB1275	Pc	1	W/T- 250C)		
			10	W(Tc=25°C)		
dissipation	2SB1236A		1	W *2		
Junction temperature		Tj	150	°C		
Storage temperature		Tstg	-55+150	°C		

●External dimensions (Units: mm)



● Packaging specifications and hFE

Туре	2SB1275	2SB1236A		
Package	CPT3	ATV		
h⊧∈	NP	PQ		
Code	TL	TV2		
Basic ordering unit (pieces)	2500	2500		

• Flectrical characteristics (Ta = 25°C)

Doron	Symbol	Min.	Turn	Max.	Unit	Conditions		
Parameter		Symbol	IVIII I.	Тур.	IVIAX.	Unit	Conditions	
Collector-base breakdown voltage		ВУсво	-160	-	-	V	$Ic = -50\mu A$	
Collector-emitter breakdown voltage		BVceo	-160	-	-	V	Ic=-1mA	
Emitter-base breakdown voltage		ВVево	-5	-	-	V	Iε = -50μA	
Collector cutoff current		Ісво	-	-	-1	μА	VcB = -120V	
Emitter cutoff current		Ієво	-	-	-1	μА	V _{EB} = -4V	
Collector-emitter saturation voltage		VcE(sat)	-	-	-2	V	Ic/IB = -1A/-0.1A	*
Base-emitter saturation voltage		V _{BE(sat)}	-	-	-1.5	V	Ic/I _B =-1A/-0.1A	*
DC current transfer ratio	2SB1275	hfe	56	-	180	-	Vc==-5V . Ic=-0.1A	
	2SB1236A		82	-	270	-	VCE = -5V , IC = -0.1A	
Transition frequency		f⊤	-	50	-	MHz	Vce = -5V, $Ie = 0.1A$, $f = 30MHz$	
Output capacitance		Cob	_	30	_	pF	Vcb = -10V , IE =0A , f = 1MHz	

^{*}Measured using pulse current.

^{* 1} Single pulse Pw=100ms
* 2 Printed circuit board 1.7mm thick, collector plating 1cm² or larger